SPECIFICATION

(300A/1700V-IGBT Module)

 Device Name
 :
 IGBT Module

 (RoHS compliant product)

 Type Name
 :
 2MBI300VN-170-50

Spec. No. : MS5F7801

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CHECKED	Apr19'-11	M.Kosaka			DWG.	WI33F7001	1/1/	

Revised Records

		Fuji Ele	ctric	Co.,Ltd.		DWG.No.	MS5F	7801	2 /
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Date Class-ification Ind. Content Applied date Drawn Checked Checked Approv	Apr19-'11	enactment	-	-	Issued date	-	S.Miyashita	M.Kosaka	O.Ikawa
	Date	Class-ification	Ind.	Content	Applied date	Drawn	Checked	Checked	Approve

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		Items	Symbols	Con	ditions	Maximum Ratings	Units
	Collec	tor-Emitter voltage	Vces			1700	V
	Gate-E	Emitter voltage	Vges			±20	V
. [Continuous	Tc=25°C	450	
rter			lc		Tc=100°C	300	1
Inverter			lc pulse	1ms		600	1
_			-lc			300	1
			-lc pulse	1ms		600	1
	Collec	tor power dissipation	Pc	1 device		1665	W
Jun	ction t	emperature	Tj			175	°C
Operating junction temperature (under switching conditions)			Тјор			150	
Storage temperature			Tstg			-40 ~ 125	1
Isolation		between terminal and copper base (*1)	Viso			3400	1/40
volta	age	between thermistor and others (*2)	VISO	AC: Imin.	AC: 1min.		VAC
Scre	ew	Mounting (*3)	-			3.5	Nm
Tor	que	Terminals (*4)	-			4.5	IN M

(*1) All terminals should be connected together during the test.

(*2) Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

(*3) Recommendable Value : 2.5-3.5 Nm (M5)

(*4) Recommendable Value : 3.5-4.5 Nm (M6)

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4. Electrical characteristics (at Tj= 25°C unless otherwise specified)

NOTICE:

The external gate resistance (Rg) shown below is one of our recommended value for the purpose of minimum switching loss. However the optimum Rg depends on circuit configuration and/or environment. We recommend that the Rg has to be carefully chosen based on consideration if IGBT module matches design criteria, for example, switching loss, EMC/EMI, spike voltage, surge current and no unexpected oscillation and so on.

	lteme	Symbolo	Condition	Conditions			CharacteristIcs			
	Items	Symbols	Condition	min.	typ.	max.	Units			
	Zero gate voltage Collector current	lces	Vge=0V, Vce=1700V	,	-	-	3.0	mA		
	Gate-Emitter leakage current	lges	Vce=0V, Vge=±20V		-	-	600	nA		
	Gate-Emitter threshold voltage	Vge(th)	Vce=20V, Ic=300mA		6.0	6.5	7.0	V		
				Tj=25°C	-	2.45	2.90			
		Vce(sat) (terminal)		Tj=125°C	-	2.90	-	1		
	Collector-Emitter	(terminal)		Tj=150°C	-	2.95	-	· · ·		
	saturation voltage	Vce(sat) (chip)	Vge=15V, Ic=300A	Tj=25°C	-	2.00	2.45			
				Tj=125°C	-	2.45	-			
ъ				Tj=150°C	-	2.50	-			
Inverter	Input capacitance	Cies	Vce=10V, Vge=0V, f	=1MHz	-	30	-	nF		
Ś		ton			-	900	-			
	Turn-on time	tr	Vcc=900V, Ic=300A, Vge=±15V, Rg=4.7Ω		-	400	-			
		tr(i)			-	100	-	nsec		
	Torra all the s	toff	Kg=4.712		-	1300	-			
	Turn-off time	tf			-	100	-			
				Tj=25°C	-	2.25	2.70	1		
		Vf (to reside 1)	Tj=125°C		-	2.55	-	1 '		
		(terminal)		Tj=150°C	-	2.55	-	- V		
	Forward on voltage		Vge=0V, If=300A	Tj=25°C	-	1.80	2.25			
		Vf (obin)		Tj=125°C	-	2.10	-			
		(chip)		Tj=150°C	-	2.10	-			
	Reverse recovery time	trr	lf=300A		-	250	-	nsec		
tor	Decistores	Р	T=25°C		-	5000	-			
Thermistor	Resistance	R	T=100°C	465	495	520	Ω			
The	B value	В	T=25/50°C		3305	3375	3450	K		

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9. Storage and transportation notes (保管·運搬上の注意事項)

The module should be stored at a standard temperature of 5 to 35°C and humidity of 45 to 75%.
 Be careful to solderability of the terminals if the module has passed over one year from manufacturing date, under the above storage condition.

常温・常湿保存が望ましい。(5~35℃,45~75%) 本保存条件下で、正常から1年以上経過した場合は端子半田付け性に十分注意すること。

- Store modules in a place with few temperature changes in order to avoid condensation on the module surface.
 急激な温度変化のなきこと。(モジュール表面が結露しないこと)
- Avoid exposure to corrosive gases and dust.
 腐食性ガスの発生場所、塵埃の多い場所は避けること。
- Avoid excessive external force on the module.
 製品に荷重がかからないように十分注意すること。
- Store modules with unprocessed terminals.
 モジュールの端子は未加工の状態で保管すること。
- Do not drop or otherwise shock the modules when transporting.
 製品の運搬時に衝撃を与えたり、落下させたりしないこと。

10. Definitions of switching time (スイッチング時間の定義)



11. Packing and labeling (梱包仕樣)

Display on the packing box

- Logo of production
- Type name
- Lot No
- Products quantity in a packing box

12. RoHS directive compliance (RoHS指令適用について)

The document (MS5F6209) about RoHS that Fuji Electric issued is applied to this IGBT Module. The Japanese Edition(MS5F6212) is made into a reference grade. 本IGBTモジュールは富士電機が発行しているRoHSに関する資料MS5F6209を適用する。 日本語版(MS5F6212)は参考資料とする。

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13. List of materials (材料リスト)



No.	Parts	Material (main)	Ref.
1	Base Plate	Cu	Ni plating
2	Terminal	Cu	Ni plating (Internal)
2	renninai	Cu	Lead free solder plating (External)
3	Cover	PPS resin	UL 94V-0
4	Case	PPS resin	UL 94V-0
5	Isolation substrate	$AI_2O_3 + Cu$	
6	IGBT chip	Silicon	(Not drawn in above)
7	FWD chip	Silicon	(Not drawn in above)
8	Thermistor	Lead glass	(Not drawn in above)
9	Wiring	Aluminum	
10	Silicone Gel	Silicone resin	
11	Adhesive	Silicone resin	
	Solder		
12	(Under chip)	Sn/Ag base	(Not drawn in above)
	(Under Isolation substrate)		
13	Label	PET	(Not drawn in above)
14	Ring	Fe	Trivalent Chromate treatment
15	Nut	Fe	Trivalent Chromate treatment
16	Terminal	Cu	Ni plating

14. Definition of switching characteristics (スイッチング特性についての定義)



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15. Reliability test result

Test cate- gories	Test items	Test methods and conditions	Reference norms EIAJ ED-4701 (Aug2001 edition)	Number of sample	Accept ance numbe
	1 Terminal Strength	Pull force : 20N (Controle terminal)	Test Method 401	5	(0:1)
	0	40N (Main terminal)	method		`````
	(Pull test)	Test time : 10±1 sec.			
	2 Mounting Strength	Screw torque : 2.5 ~ 3.5 N·m (M5)	Test Method 402	5	(0:1)
		: 3.5 ~ 4.5 N·m (M6)	method		
		Test time : 10±1 sec.			
	3 Vibration	Range of frequency : 10 ~ 500Hz	Test Method 403	5	(0:1
		Sweeping time : 15 min.	Reference 1		
		Acceleration : 100m/s ²	Condition code B		
6		Sweeping direction : Each X,Y,Z axis			
Mechanical Tests		Test time : 6 hr. (2hr./direction)			
al T	4 Shock	Maximum accelerat : 5000m/s ²	Test Method 404	5	(0:1
anic		Pulse width : 1.0msec.	Condition code B		
che		Direction : Each X,Y,Z axis			
Me	-	Test time : 3 times/direction	T (M () 000		(
	⁵ Solderabitlity	Solder temp. : 245 ± 5 °C	Test Method 303	5	(0:1
		Immersion time : 5 ± 0.5 sec.	Condition code A		
		Test time : 1 time			
		Each terminal should be Immersed in solde within 1 ~ 1.5mm from the body.	r		
	⁶ Resistance to	Solder temp. : $260 \pm 5 \text{ °C}$	Test Method 302	5	(0:1
	Soldering Heat	Immersion time : 10 ± 1 sec.	Condition code A		
		Test time : 1 time			
		Each terminal should be Immersed in solde within 1 ~ 1.5mm from the body.	r		
	1 High Temperature	Storage temp. : 125 ± 5 °C	Test Method 201	5	(0:1)
	Storage 2 Low Temperature	Test duration : 1000hr.	Test Method 202	5	(0:1
	Storage	Storage temp. : $-40 \pm 5 \degree C$ Test duration : 1000hr.	Test Method 202	5	(0.1
	3 Temperature	Storage temp. : $85 \pm 2 \ ^{\circ}C$	Test Method 103	5	(0:1
	Humidity	Relative humidity : $85 \pm 5\%$	Test code C	Ŭ	(0.1
	Storage	Test duration : 1000hr.			
	⁴ Unsaturated	Test temp. : 120 ± 2 °C	Test Method 103	5	(0:1
ŝ	Pressurized	Test humidity : 85 ± 5%	Test code E		,
est	Vapor	Test duration : 96hr.			
hΤ	5 Temperature	Low temp40 ± 5 °	C Test Method 105	5	(0:1
Environment Tests	Cycle	Test temp. : High temp. 125 ± 5			
iuo.		RT 5~35 °C			
nvir		Dwell time : High ~ RT ~ Low ~	RT		
ш		1hr. 0.5hr. 1hr. 0.	5hr.		
		Number of cycles : 100 cycles			
	6 Thermal Shock	Test temp. : High temp. 100 ⁺⁰ .	5 °C Test Method 307	5	(0:1
			method		
		Used liquid : Water with ice and boiling water	Condition code B		
		Dipping time : 5 min. par each ten	np.		
		Transfer time : 10 sec.			
		Number of cycles : 10 cycles			
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Reliability Test Items

Test cate- gories	Test items	Test m	eth	nods and conditions	Reference norms EIAJ ED-4701 (Aug2001 edition)	Number of sample	Accept- ance number
	1 High temperature				Test Method 101	5	(0:1)
	Reverse Bias	Test temp.	:	Tj = 150 (-0 /+5)			
	(for Collector -						
	Emitter) Bias Voltage	:	VC = 0.8×VCES			
		Bias Method	:	Applied DC voltage to C-E VGE = 0V			
		Test duration	:	1000hr.			
	2 High temperature				Test Method 101	5	(0:1)
	Bias (for gate)	Test temp.	:	Tj = 150 (-0 /+5)			
ts		Bias Voltage	:	VC = VGE = +20V or -20V			
Endurance Tests		Bias Method	:	Applied DC voltage to G-E VCE = 0V			
ranc		Test duration	:	1000hr.			
npu	3 Temperature				Test Method 102	5	(0:1)
ш	Humidity Bias	Test temp.	:	85±2 °C	Condition code C		
		Relative humidi	:	85±5%			
		Bias Voltage	:	VC = 0.8×VCES			
		Bias Method	:	Applied DC voltage to C-E			
				VGE = 0V			
		Test duration	:	1000hr.			
	4 Intermitted	ON time	:	2 sec.	Test Method 106	5	(0:1)
	Operating Life	OFF time	:	18 sec.			
	(Power cycle)	Test temp.	:	100±5 deg			
	(for IGBT)			Tj 150 , Ta=25±5			
		No. of cycles	:	15000 cycles			

Reliability Test Items

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Failure Criteria

lto m	Charact	Characteristic		Failure crite	eria	Unit	Note
Item	Characte			Lower limit	Upper limit		
Electrical	Leakage current		ICES	-	USL×2	mA	
characteristic			±IGES	-	USL×2	μΑ	
	Gate threshold	voltage	VGE(th)	LSL×0.8	USL×1.2	mA	
	Saturation volta	age	VCE(sat)	-	USL×1.2	V	
	Forward voltage		VF	-	USL×1.2	V	
	Thermal	IGBT	Δ VGE		USL×1.2	mV	
	resistance		or Δ VCE	-	U3LX1.2		
		FWD	ΔVF	-	USL×1.2	mV	
	Isolation voltage		Viso	Broken insulation		-	
Visual	Visual inspection	on					
inspection	Peeling Plating and the others			The visual sample		-	
			-	The visual sample		-	

Note :

USL : Upper specified limit.

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Each parameter measurement read-outs shall be made after stabilizing the components at room ambient for 2 hours minimum, 24 hours maximum after removal from the tests. And in case of the wetting tests, for example, moisture resistance tests, each component shall be made wipe or dry completely before the measurement.

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Reliability Test Results

Test cate- gories		Test items	Reference norms EIAJ ED-4701 (Aug2001 edition)	Number of test sample	Number of failure sample
	1	Terminal Strength (Pull test)	Test Method 401 Method	5	0
-	2	Mounting Strength	Test Method 402	5	0
	2		method	Ŭ	Ű
Mechanical Tests	3	Vibration	Test Method 403	5	0
al Te			Condition code B		_
anic	4	Shock	Test Method 404	5	0
acha			Condition code B		
ž	5	Solderabitlity	Test Method 303	1 303 5	0
			Condition code A		
	6	Resistance to Soldering Heat	Test Method 302	5	0
			Condition code A		
	1	High Temperature Storage	Test Method 201	5	0
	2	Low Temperature Storage	Test Method 202	5	0
ests	3	Temperature Humidity	Test Method 103	5	0
nt Te		Storage	Test code C		
Environment Tests	4	Unsaturated	Test Method 103	5	0
iron		Pressurized Vapor	Test code E		
Еnv	5	Temperature Cycle	Test Method 105	5	0
	6	Thermal Shock	Test Method 307	5	0
			method		
			Condition code A		
	1	High temperature Reverse Bias	Test Method 101	5	0
ests	2	High temperature Bias	Test Method 101	5	0
e Τέ		(for gate)			
Endurance Tests	3	Temperature Humidity Bias	Test Method 102	5	0
Inpu			Condition code C		
Ē	4	Intermitted Operating Life (Power cycling) (for IGBT)	Test Method 106	5	0

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Warnings			
This product shall be used within its maximum rating (voltage, cur may be broken in case of using beyond the maximum ratings. If P main pin terminals may have higher temperature than Tstg. Also 製品の最大定格(電圧,電流,温度等)の範囲内で御使用下さい。最 破壊する場合があります。また、使用するプリント板が不適切な場合、 あります。主端子ピンもTstg範囲内でご使用下さい。	rinte he p 大定相	d Circuit Board is not suitabl in terminals shall be used wi 各を超えて使用すると、素子が	e, the thin Tstg. t
Connect adequate fuse or protector of circuit between three-phas equipment from causing secondary destruction, such as fire, its s 万一の不慮の事故で素子が破壊した場合を考慮し、商用電源と本製。 を必ず付けて火災,爆発,延焼等の2次破壊を防いでください。	oread	ding, or explosion.	
Use this product after realizing enough working on environment a This product may be broken before target life of the system in cas life. 製品の使用環境を十分に把握し、製品の信頼性寿命が満足できるか	e of	using beyond the product's	reliability
信頼性寿命を超えて使用した場合、装置の目標寿命より前に素子が			
If the product had been used in the environment with acid, organic sulfide, sulfurous acid gas), the product's performance and appea 酸・有機物・腐食性ガス(硫化水素,亜硫酸ガス等)を含む環境下で使 できません。	ranc	e can not be ensured easily.	-
Use this product within the power cycle curve (Technical Rep.No. classified to delta-Tj mode which is stated as above and delta-Tc down of case temperature (Tc), and depends on cooling design o application which has such frequent rise and down of Tc, well cor 本製品は、パワーサイクル寿命カーブ以下で使用下さい(技術資料No cのATj による場合の他に、ATcによる場合があります。これはケース本製品をご使用する際の放熱設計に依存します。ケース温度の上昇 留意してご使用下さい。	mod f equ sider o.: M ⁻ .温度	e. Delta-Tc mode is due to ri ipment which use this produ ration of product life time is r T5F12959)。パワーサイクル而 (Tc)の上昇下降による熱スト	se and loct. In necessary. 対量には レスであり、
Never add mechanical stress to deform the main or control termir poor contact problem. 主端子及び制御端子に応力を与えて変形させないで下さい。 端子の があります。		he deformed terminal may c により、接触不良などを引きま	
Use this product with keeping the cooling fin's flatness between s the roughness within 10um. Also keep the tightening torque within convex of cooling fin may cause isolation breakdown and this may hand, too large concave of cooling fin makes gap between this pr conductivity will be worse and over heat destruction may occur. 冷却フィンはネジ取り付け位置間で平坦度を100mmで50um以下、表な凸反りがあったりすると本製品が絶縁破壊を起こし、重大事故に発,やゆがみ等があると、本製品と冷却フィンの間に空隙が生じて放熱が	i the / lead oduc 面の 展する	limits of this specification. To d to a critical accident. On th t and the fin bigger, then, the 粗さは10um以下にして下さい る場合があります。また、過大:	oo large e other ermal い。過大 な凹反り
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Warnings	5
 In case of mounting this product on cooling fin, use thermal compound amount was not enough or its applying meterough, then, thermal conductivity will be worse and thermal Confirm spreading state of the thermal compound when its ap (Spreading state of the thermal compound can be confirmed) 素子を冷却フィンに取り付ける際には、熱伝導を確保するためのとしたり、塗布方法が不適だったりすると、コンパウンドが十分に素事があります。 コンパウンドを塗布する際には、製品全面にコンパウンドが広がき(実装した後に素子を取りはずすとコンパウンドの広がり具合を確 	ethod was not suitable, its spreading will not be run away destruction may occur. oplying to this product. by removing this product after mounting.) コンパウンド等をご使用ください。又、塗布量が不足 子全体に広がらず、放熱悪化による熱破壊に繋がる
 It shall be confirmed that IGBT's operating locus of the turn-of specification. This product may be broken if the locus is out o ターンオフ電圧・電流の動作軌跡がRBSOA仕様内にあることを研 と素子が破壊する可能性があります。 	f the RBSOA.
 If excessive static electricity is applied to the control terminals countermeasures against static electricity. 制御端子に過大な静電気が印加された場合、素子が破壊する場 して下さい。 	
 Never add the excessive mechanical stress to the main or co equipments. The module structure may be broken. 素子を装置に実装する際に、主端子や制御端子に過大な応力を あります。 	
 In case of insufficient -VGE, erroneous turn-on of IGBT may of this malfunction. (Recommended value : -VGE = -15V) 逆バイアスゲート電圧-VGEが不足しますと誤点弧を起こす可能性 十分な値で設定して下さい。(推奨値: -VGE = -15V) 	
 In case of higher turn-on dv/dt of IGBT, erroneous turn-on of of in the most suitable drive conditions, such as +VGE, -VGE, R ターンオン dv/dt が高いと対向アームのIGBTが誤点弧を起こす ドライプ条件(+VGE, -VGE, RG, CGE)でご使用下さい。 	G, CGE to prevent the malfunction.
 This product may be broken by avalanche in case of VCE be C-E terminals. Use this product within its maximum voltage. VCESを超えた電圧が印加された場合、アバランシェを起こして素の範囲内でご使用下さい。 	
 In case of soldering this product at excessive heat condition, Please handle with care for soldering process. 製品を過大な温度で半田付けした場合、パッケージの劣化を引起 ご使用ください。 	
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